



# STPS16150CT/CG/CR

## HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

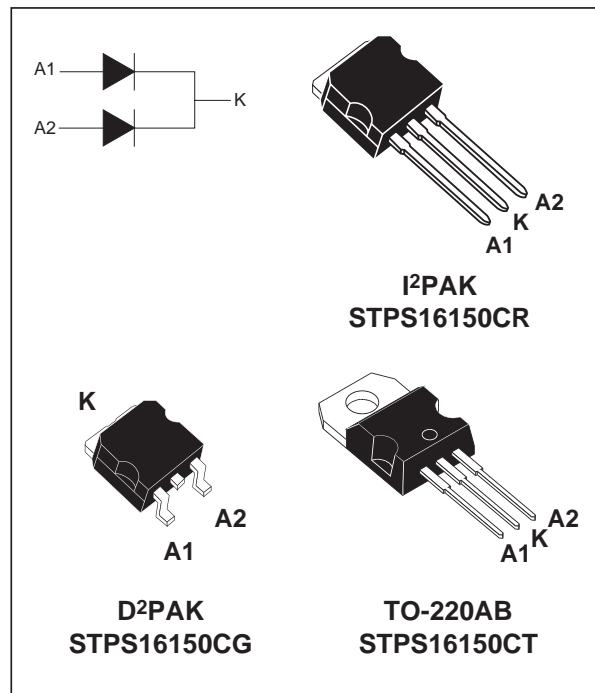
$I_{F(AV)}$	<b>2 x 8 A</b>
$V_{RRM}$	<b>150 V</b>
$T_j$	<b>175°C</b>
$V_F$ (max)	<b>0.75 V</b>

### FEATURES AND BENEFITS

- HIGH JUNCTION TEMPERATURE CAPABILITY
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW LEAKAGE CURRENT
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Dual center tap schottky rectifier designed for high frequency Switched Mode Power Supplies.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage			150	V
$I_{F(RMS)}$	RMS forward current			20	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AB D²PAK / I²PAK	$T_c = 150^\circ\text{C}$ per diode per device	8 16	A
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10 \text{ ms}$ sinusoidal	150	A
$P_{ARM}$	Repetitive peak avalanche power		$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	4700	W
$T_{stg}$	Storage temperature range			- 65 to + 175	°C
$T_j$	Maximum operating junction temperature			175	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/ $\mu\text{s}$

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## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit	
$R_{th(j-c)}$	Junction to case	TO-220AB / D <sup>2</sup> PAK / I <sup>2</sup> PAK	Per diode	3	°C/W
			Total	1.8	
$R_{th(c)}$		TO-220AB / D <sup>2</sup> PAK / I <sup>2</sup> PAK	Coupling	0.6	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

## STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit	
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			3.0	$\mu\text{A}$	
		$T_j = 125^\circ\text{C}$				4.0	mA	
$V_F^{**}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8\text{ A}$			0.92	V	
		$T_j = 125^\circ\text{C}$			0.70	0.75		
		$T_j = 25^\circ\text{C}$		$I_F = 16\text{ A}$				1
		$T_j = 125^\circ\text{C}$			0.8	0.86		

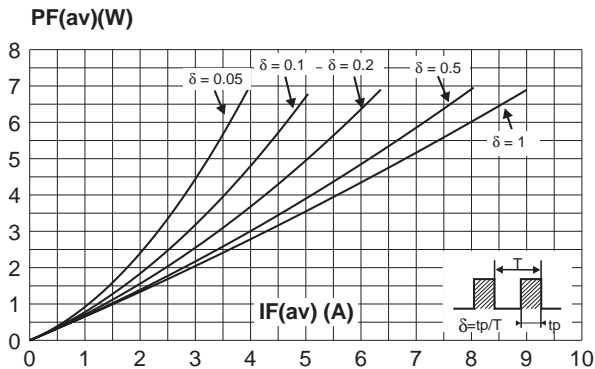
Pulse test : \*  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

\*\*  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

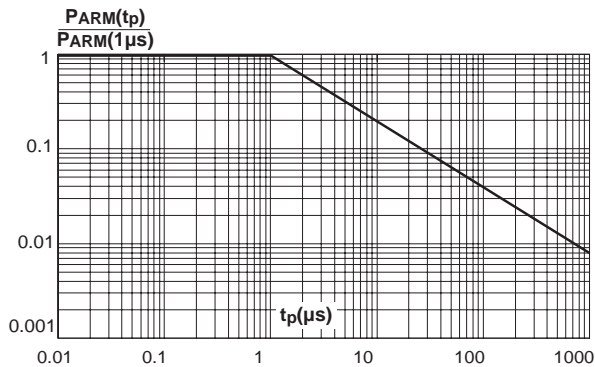
To evaluate the conduction losses use the following equation:

$$P = 0.64 \times I_{F(AV)} + 0.014 I_{F(RMS)}^2$$

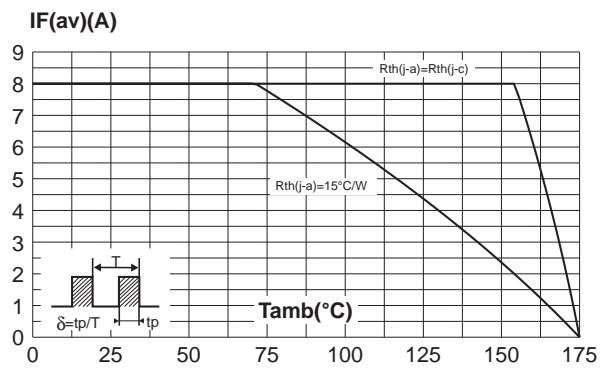
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



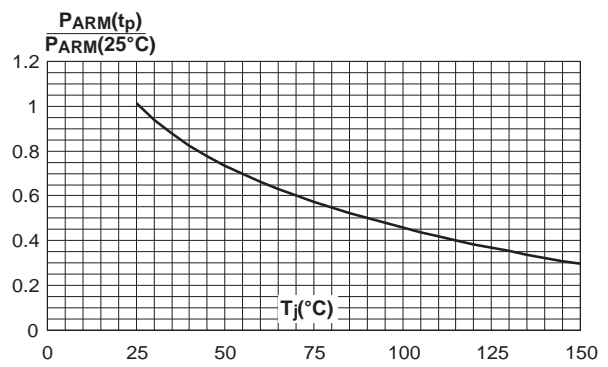
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



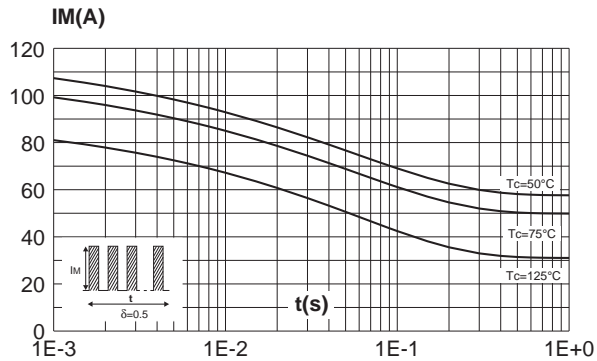
**Fig. 2:** Average forward current versus ambient temperature ( $\delta = 0.5$ , per diode).



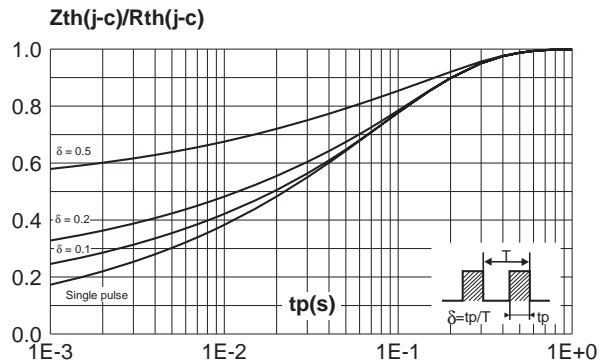
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



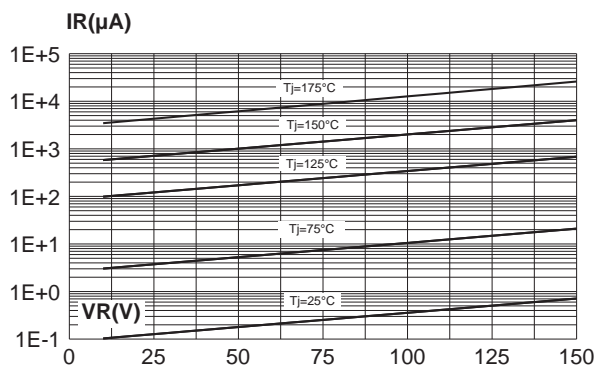
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



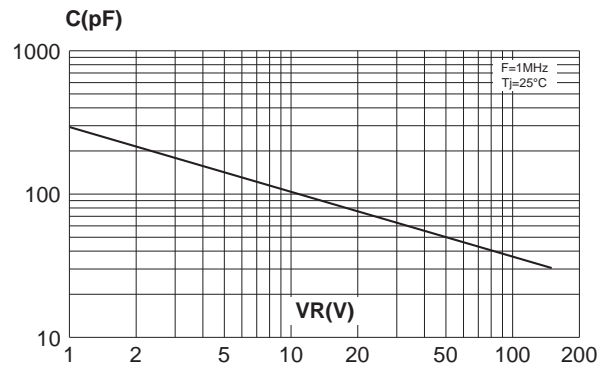
**Fig. 46** Relative variation of thermal impedance junction to case versus pulse duration (per diode).



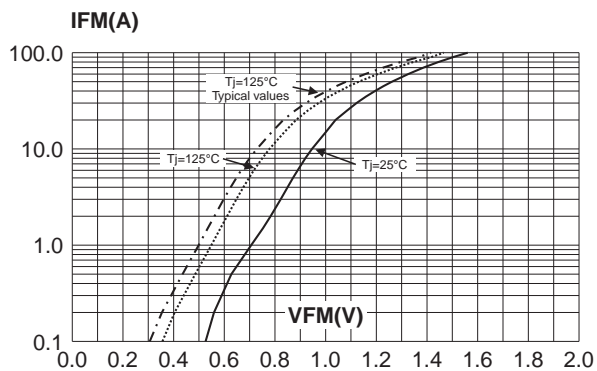
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values, per diode).



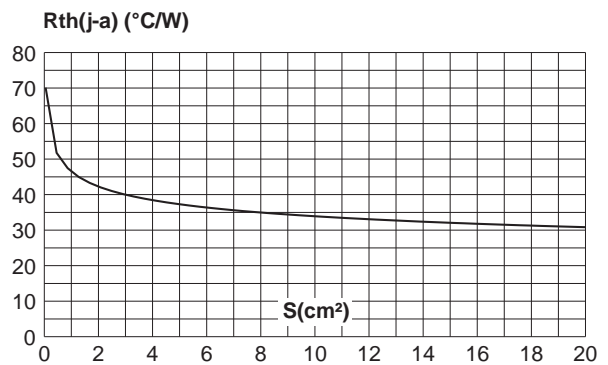
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values, per diode).



**Fig. 9:** Forward voltage drop versus forward current (maximum values, per diode).

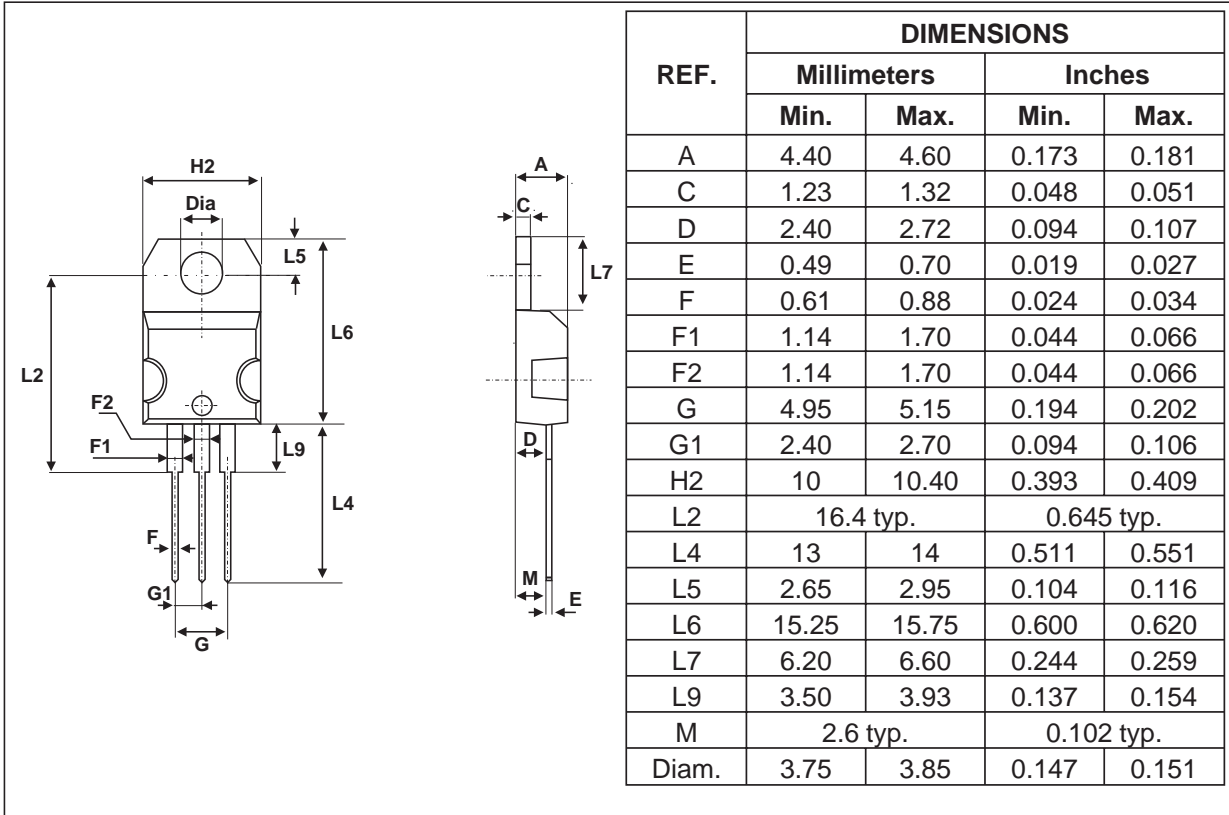


**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: 35 $\mu\text{m}$ ) (STPS16150CG only).

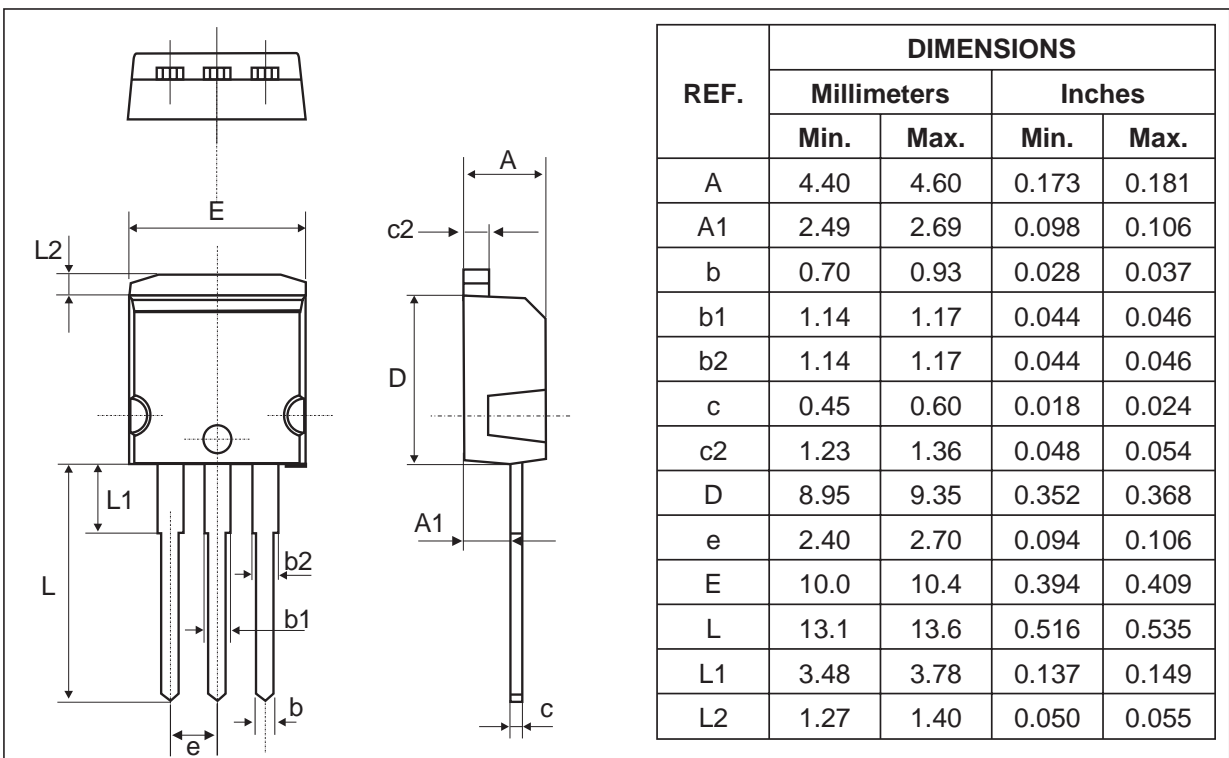


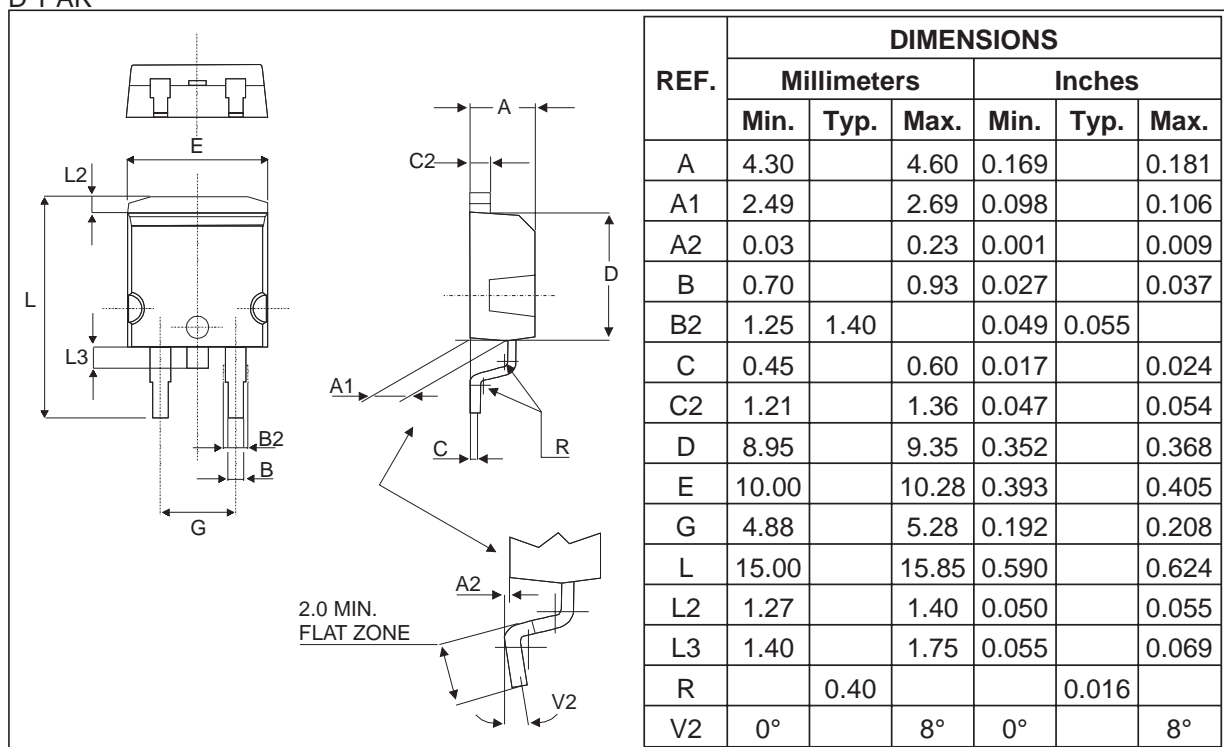
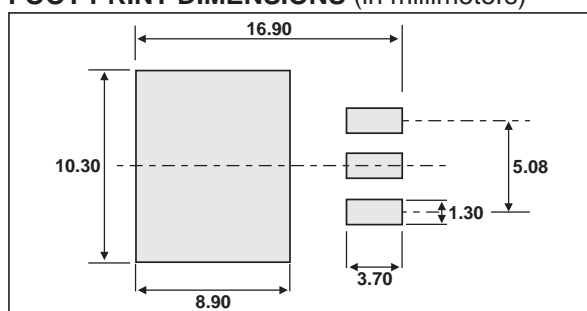
**STPS16150CT/CG/CR**

**PACKAGE MECHANICAL DATA**  
TO-220AB



**PACKAGE MECHANICAL DATA**  
I<sup>2</sup>PAK



**PACKAGE MECHANICAL DATA**  
**D<sup>2</sup>PAK**

**FOOT PRINT DIMENSIONS (in millimeters)**


Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS16150CT	STPS16150CT	TO-220AB	2.2 g	50	Tube
STPS16150CG	STPS16150CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS16150CG-TR	STPS16150CG	D <sup>2</sup> PAK	1.48 g	1000	Tape & reel
STPS16150CR	STPS16150CR	I <sup>2</sup> PAK	1.49 g	50	Tube

**■ Epoxy meets UL94, V0**

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